



DMG2301L

#### P-CHANNEL ENHANCEMENT MODE MOSFET

# **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	120mΩ @ V <sub>GS</sub> = -4.5V	
-20V	150mΩ @ V <sub>GS</sub> = -2.5V	-3A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

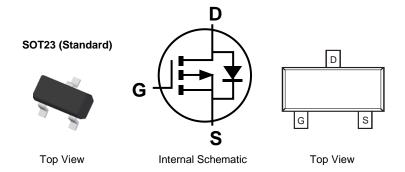
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

## **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 63
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



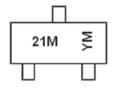
# Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2301L-7	SOT23 (Standard)	3,000/Tape & Reel
DMG2301L-13	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

## **Marking Information**



21M = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M = Month (ex: 9 = September)

#### Date Code Key

Year	2014		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	В			J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage			Vgss	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	I <sub>D</sub>	-3 -1	А	
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-10	Α	
Drain-Source Diode Forward Current (t < 5 sec)			Is	-0.75	А

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	83	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

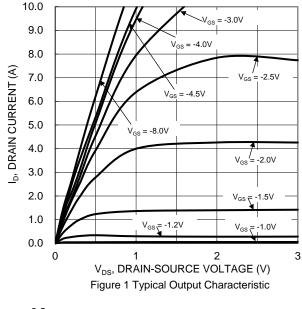
# Electrical Characteristics (@TA = +25°C, unless otherwise specified)

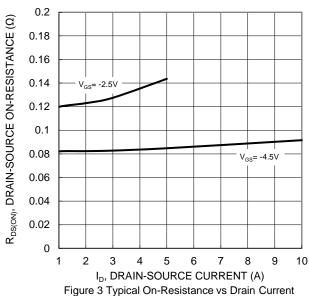
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				I.	l .	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	Vgs = 0V, ID = -250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 6V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	-0.4	_	-1.2	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
Static Drain-Source On-Resistance	Dagger			120	mΩ	$V_{GS} = -4.5V$ , $I_{D} = -2.8A$
Static Dialii-Source Off-Nesistance	RDS(ON)			150	11122	$V_{GS} = -2.5V$ , $I_D = -2.0A$
Diode Forward Voltage	VsD	_		-1.2	V	$V_{GS} = 0V$ , $I_{S} = -0.75A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		476	—	pF	\/ 10\/ \/ 0\/
Output Capacitance	Coss	_	53	—	pF	$V_{DS} = -10V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	$C_{rss}$	_	45	_	pF	1 = 1.01/11/12
Total Gate Charge	Qg	_	5.5		nC	
Gate-Source Charge	$Q_{gs}$	_	0.9	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -6V$ , $I_{D} = -2.8A$
Gate-Drain Charge	$Q_{gd}$	_	1.8	_	nC	
Turn-On Delay Time	tD(ON)	_	5	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	10	_	ns	$V_{DS} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	tD(OFF)	_	30	_	ns	$R_{GEN} = 6\Omega$ , $I_D = -1A$
Turn-Off Fall Time	t <sub>F</sub>	_	20	_	ns	

Notes:

- 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







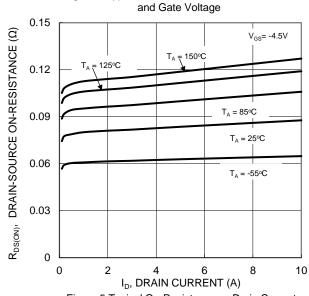
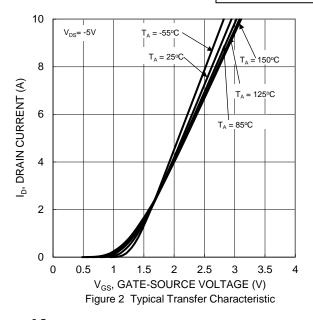
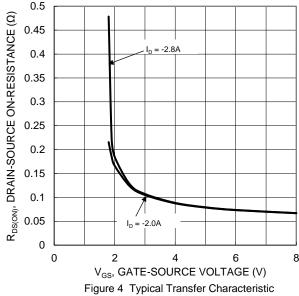


Figure 5 Typical On-Resistance vs Drain Current and Temperature





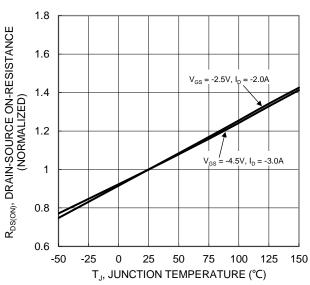


Figure 6 On-Resistance Variation with Temperature



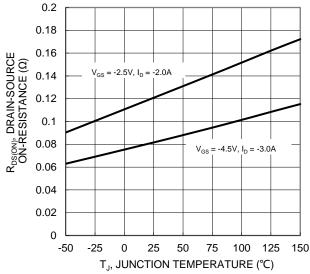


Figure 7 On-Resistance Variation with Temperature

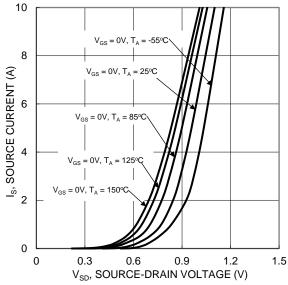
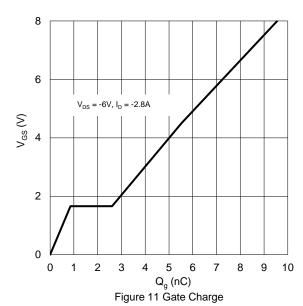


Figure 9 Diode Forward Voltage vs. Current



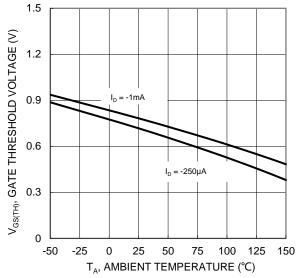
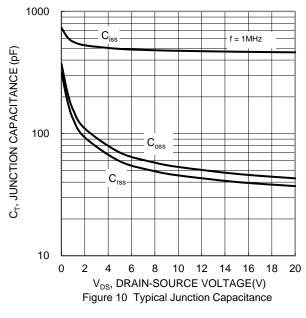


Figure 8 Gate Threshold Variation vs Ambient Temperature



100

R<sub>DS(ON)</sub>
Limited

R<sub>DS(ON)</sub>
R<sub>DS(ON)</sub>
Limited

R<sub>DS(ON)</sub>
R



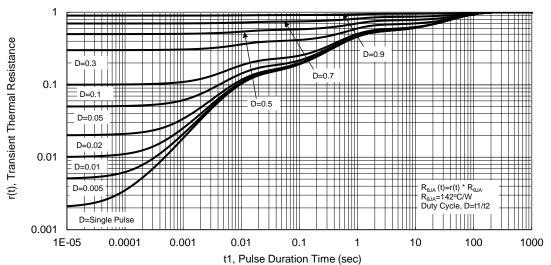


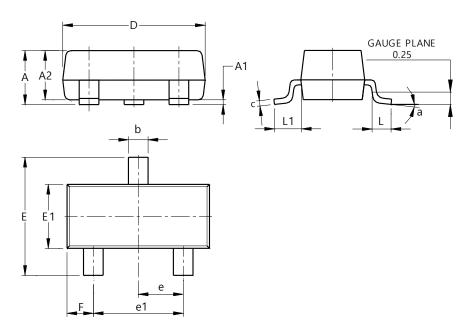
Figure 13 Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23 (Standard)

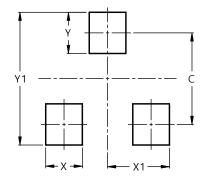


SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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